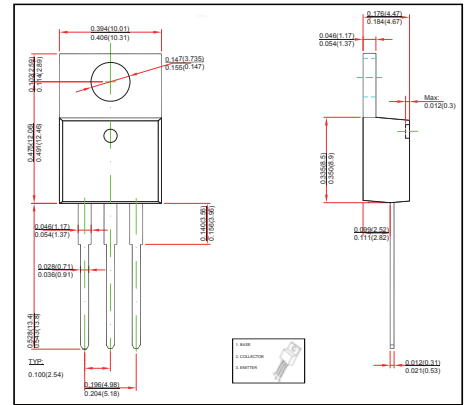


TO-220 Plastic-Encapsulate Transistors
FEATURES

- Power switching applications
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-220L molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	700	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current -Continuous	I_C	1.5	A
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Electrical Specification ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=5\text{mA}, I_E=0$	700			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=2\text{mA}, I_C=0$	9			V
Collector cut-off current	I_{CBO}	$V_{CB}=700\text{V}, I_E=0$			1	mA
Collector cut-off current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			0.5	mA
Emitter cut-off current	I_{EBO}	$V_{EB}=9\text{V}, I_C=0$			1	mA
DC current gain	hFE1	$V_{CE}=5\text{V}, I_C=0.5\text{A}$	8		40	
	hFE2	$V_{CE}=5\text{V}, I_C=1.5\text{A}$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=0.25\text{A}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=0.25\text{A}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=1\text{MHz}$	5			MHz
Fall time	t_f	$I_C=1\text{A}, I_{B1}=-I_{B2}=0.2\text{A}, V_{CC}=100\text{V}$			0.5	μs
Storage time	t_s	$I_C=250\text{mA}$	2		4	μs